

Amendments to the Claims:

Please cancel claims 1 - 11 without prejudice or disclaimer of the subject therein and add the following new claims.

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 11 (canceled)

12. (new) A plasma processing apparatus for processing a product using plasma, comprising:

a power source for applying bias power to an electrode on which a substrate to be processed is disposed;

an insulating layer formed on a surface of said electrode on which said substrate to be processed is disposed;

a first conductive material formed within said insulating layer;

a first feeder line connecting said power source and said first conductive material;

a first variable capacitor provided in said first feeder line;

a silicon ring mounted at a position surrounding the substrate to be processed, on the surface of said electrode on which the substrate to be processed is disposed;

a second conductive material formed within said insulating layer and under said silicon ring;

a second feeder line connecting said power source and said second conductive material; and

a second variable capacitor provided in said second feeder line.

13. (new) The apparatus according to claim 12, wherein said insulating layer formed on the surface of said electrode includes alumina.

14. (new) The apparatus according to claim 13, wherein said insulating layer at a position where said first conductive material and said second conductive material are formed has a thickness which is greater than a thickness of said insulating layer at another position where said first conductive material and said second conductive material are not formed.

15. (new) The apparatus according to claim 14, wherein a part of said insulating layer is disposed under said first conductive material and said second conductive material and between said first conductive material and said electrode and between said second conductive material and said electrode, the another position of said insulating layer being a center portion thereof.

16. (new) A plasma processing apparatus for processing a product using plasma, comprising:

a high-frequency power source for applying bias power to an electrode on which a substrate to be processed is disposed;

an insulating layer formed on a surface of said electrode on which said substrate to be process is disposed;

a conductive material formed within said insulating layer;
a feeder line connecting said high-frequency power source and said conductive material;
a variable capacitor provided in said feeder line; and
a direct current power source connected between said electrode and said high-frequency power source.

17. (new) The apparatus according to claim 15, wherein a first resonance coil is coupled to said variable capacitor provided on said feeder line, and a second resonance coil is provided between said direct current power source and said electrode.